

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S11 2	65550	(amorphous\$4 alpha noncrystal\$6) near (silicon si!) "a-si"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 17:59
S13 8	71401	(amorphous\$4 alpha noncrystal\$6) near (silicon si!) "a-si" ".alpha." adj Si	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 18:37
S13 9	71401	(amorphous\$4 alpha noncrystal\$6) near (silicon si!) "a-si" ".alpha." adj Si ".alpha.-si"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 18:37
S14 0	71401	(amorphous\$4 alpha noncrystal\$6) near (silicon si!) "a-si" ".alpha." adj Si ".alpha.-si" ".alpha.-si"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 18:38
S14 1	83894	tft thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 18:38
S14 2	1602568	channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 18:38
S14 3	896	S140 near4 S141 with S142	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 18:40
S14 4	744	S143 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 18:41
S14 5	1894	S140 with S141 with S142	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 18:41
S14 6	314535	inplant or implant or inplanting or implanting dopant doping	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 18:40

S14 7	82	S140 with S141 with S146 with S142	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:14
S14 8	75	S147 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:23
S14 9	0	S140 with S141 with light\$4 near2 (dopant doping) with S142	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:14
S15 0	0	S140 with light\$4 near2 (dopant doping) with S142 and S141	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:15
S15 2	0	S140 with ("n.sup.-" "p.sup.-") with S142 and S141	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:17
S15 3	162	("n.sup.-" "p.sup.-")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:16
S15 4	0	S140 with ("n.sup." "p.sup.") with S142 and S141	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:22
S15 5	19044	ldd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:18
S15 6	6594	ldd with (n p)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:18
S15 7	796	S140 with ("n- " "p- ") with S142 and S141	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:23

S15 8	471	S140 with ("n- " "p- ") with S142 with S141	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:24
S15 9	401	S158 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:24
S16 0	471	S140 with (n-! p-!) with S142 with S141	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 19:24
S16 1	401	S160 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:58
S16 2	71478	(amorphous\$4 alpha noncrystal\$6) near (silicon si!) "a-si" ".alpha." adj Si ".alpha.-si" ".alpha."-si	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:58
S16 3	84035	tft thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:58
S16 4	1604098	channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:58
S16 5	472	S162 with (n-! p-!) with S164 with S163	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 14:58
S16 6	401	S165 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:07
S16 7	118101	(cubic cubed) near (centimeter cm) "cm.sup.3" "cm.sup.-3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:06

S16 8	0	"cm.sup.-3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:00
S16 9	0	"cm.sup.-3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:00
S17 0	0	"cm.sup.-3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:06
S17 1	91761	"cm.sup.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:00
S17 2	1470	(atom ion) adj (centimeter cm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:01
S17 3	0	"cm.sup.-2."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:06
S17 4	118101	(cubic cubed) near (centimeter cm) "cm.sup.3" "cm-.sup.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 15:06
S17 5	20	S162 with S164 and light\$4 near2 (dopant doping) with S164 and S163	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:11
S17 6	71478	(amorphous\$4 alpha noncrystal\$6) near (silicon si!) "a-si" ".alpha." adj Si ".alpha.-si" ".alpha."-si	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:11
S17 7	84035	tft thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:14

S17 8	1604098	channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:11
S17 9	20	S176 with S178 and light\$4 near2 (dopant doping) with S178 and S177	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:12
S18 0	4517	S176 with (rate speed (nm nanometer angstrom ang) adj (sec second min minute))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:13
S18 1	1947	S176 with (rate speed (nm nanometer angstrom ang) adj (sec second min minute)) and S177	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:13
S18 2	249	S176 with (rate speed (nm nanometer angstrom ang) adj (sec second min minute)) same S178 and S177	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:15
S18 3	213	S182 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:15
S18 4	84035	tft thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:54
S18 5	249	S176 with (rate speed (nm nanometer angstrom ang) adj (sec second min minute)) same S178 and S184	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:32
S18 6	213	S185 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:34
S18 7	442421	(phosphorus phosphine "ph.sub.3" boron boroethane "b.sub.2h.sub.6" "b. sub.2 h.sub.6")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:29

S18 8	15993	S187 with (S178 or S176)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:53
S18 9	79	S186 and S188	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:31
S19 0	70	S176 with (deposit\$6) near2 (chang\$4 differ\$4 high\$4 low\$4 fast\$4 slow\$4) same S178 and S184	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:35
S19 1	16	S188 and S190	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:34
S19 2	213	S186 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:34
S19 3	12	S191 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:37
S19 4	1650	S176 with (deposit\$6) near2 (chang\$4 differ\$4 high\$4 low\$4 fast\$4 slow\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:51
S19 5	149	S188 and S194 and S184	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:37
S19 6	133	S195 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:37
S19 7	71478	(amorphous\$4 alpha noncrystal\$6) near (silicon si!) "a-si" ".alpha." adj Si ".alpha.-si" ".alpha."-si	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:51

S19 8	1650	S197 with (deposit\$6) near2 (chang\$4 differ\$4 high\$4 low\$4 fast\$4 slow\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 18:18
S19 9	1604098	channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:53
S20 0	442421	(phosphorus phosphine "ph.sub.3" boron boroethane "b.sub.2h.sub.6" "b. sub.2 h.sub.6")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:53
S20 1	15993	S200 with (S199 or S197)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 18:02
S20 2	396	S198 and S201	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:54
S20 3	84035	tft thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:54
S20 4	149	S202 and S203	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 17:54
S20 5	133	S204 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 18:05
S20 6	49188	(phosphorus boron n-type p-type n adj type p adj type) with (S199 or S197)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 18:04
S20 7	212	S198 and S206 and S203	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 18:05

S208	187	S207 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 18:05
S209	37	S197 with (deposit\$6) near2 (chang\$4 differ\$4 high\$4 low\$4 fast\$4 slow\$4) with S199 and S203	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 18:19
S210	2	"6222214".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 17:43
S211	2	S210 and (source drain s/d electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 17:43
S212	84083	tft thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 17:58
S213	1604710	channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 17:58
S214	9662	"atoms/cm.sup.3" "ions/cm.sup.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 17:58
S215	91805	"cm.sup.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 17:58
S216	1322476	concentration	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 17:58
S217	487	S212 same S213 with (boron phosphorous phosphine "ph.sub.3" boroethane "b.sub.2h.sub.6" "b.sub.2h.sub.6") with (S214 S215 S216)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:04

S21 8	403	S217 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:05
S21 9	71519	(amorphous\$4 alpha noncrystal\$6) near (silicon si!) "a-si"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:07
S22 0	2077	S219 near4 S213	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:00
S22 1	26	S218 and S220	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:00
S22 2	22371	(boron phosphorous phosphine "ph. sub.3" boroethane "b.sub.2h.sub.6" "b.sub.2 h.sub.6") with (S214 S215 S216)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:04
S22 3	190	S212 and S213 same S219 same S222	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:07
S22 4	170	S223 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:08
S22 5	190	S212 and S213 same ((amorphous\$4 alpha noncrystal\$6) near (silicon si!) or "a-si") same S222	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:10
S22 6	170	S225 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:09
S22 7	182	S212 and S213 same ((amorphous\$4 alpha noncrystal\$6) near (silicon si!)) same S222	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:08

S22 8	164	S227 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:10
S22 9	210	S212 and S213 same ((amorphous\$4 alpha noncrystal\$6) or "a-si") same S222	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:10
S23 0	180	S229 and (@ad < "20040211")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:15
S23 1	15585	(semiconductor adj energy).as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:15
S23 2	84	S230 not S231	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:43
S23 3	2	"6801293".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:45
S23 4	0	S233 and (S214 S215)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:45
S23 5	2	"6833333".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:45
S23 6	0	S235 and (S214 S215)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:46
S23 7	0	S235 and (S214 S215 S216)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/04 18:46

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7138	((438/30) or (438/149) or (438/161) or (438/311) or (438/479) or (438/482) or (438/586) or (438/761)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/17 18:33